

TO-92 Plastic-Encapsulate Transistors

A42 TRANSISTOR (NPN)

FEATURES

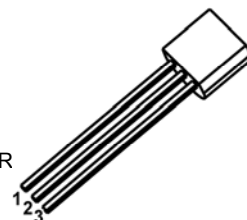
- High voltage

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	310	V
V_{CE0}	Collector-Emitter Voltage	305	V
V_{EB0}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	200	mA
I_{CM}	Collector Current -Pulsed	500	mA
P_C	Collector Power Dissipation	625	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, junction to Ambient	200	$^\circ\text{C}/\text{mW}$
$R_{\theta JC}$	Thermal Resistance, unction to Case	83.3	$^\circ\text{C}/\text{mW}$

TO-92

1. EMITTER
2. BASE
3. COLLECTOR



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	310			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$, $I_B=0$	305			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$, $I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=200\text{V}$, $I_E=0$			0.25	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10\text{V}$, $I_C=1\text{mA}$	60			
	$h_{FE(2)}$	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$	80		250	
	$h_{FE(3)}$	$V_{CE}=10\text{V}$, $I_C=30\text{mA}$	75			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=20\text{mA}$, $I_B=2\text{mA}$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=20\text{mA}$, $I_B=2\text{mA}$			0.9	V
Transition frequency	f_T	$V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=30\text{MHz}$	50			MHz

CLASSIFICATION OF $h_{FE(2)}$

Rank	A	B ₁	B ₂	C
Range	80-100	100-150	150-200	200-250